

AMENDMENT TO THE CLAIMS

1. (Currently amended) An electret condenser, comprising:

a first electrode;

a second electrode;

a first insulating film which is formed between the first electrode and the second electrode and is electretized; and

a second insulating film formed so as to cover upper, lower and side surfaces of the first insulating film,

wherein the first insulating film covered with the second insulating film is formed on the second electrode, and

the second electrode, the first insulating film, and the second insulating film compose a vibrating film.

2. (Previously presented) A method for manufacturing the electret condenser of Claim 1, wherein the first insulating film is a silicon dioxide film grown in an atmosphere at a temperature in a range between 500 °C and 800 °C, both inclusive.

3. (Previously presented) A method for manufacturing the electret condenser of Claim 1, wherein the second insulating film is a silicon nitride film grown in an atmosphere at a temperature in the range between 600 °C and 800 °C, both inclusive

4. (Cancelled)

5. (Currently Amended) The electret condenser of Claim [[4]] 1,
wherein a shape in plan of the first insulating film is smaller than a shape in plan of the
vibrating film, and
the first insulating film is arranged at a central part of the vibrating film.

6. (Currently amended) An electret condenser, comprising:
a first electrode;
a second electrode; and
a first insulating film which is formed between the first electrode and the second
electrode and is electretized,
wherein a lower surface of the first insulating film is covered with the second electrode
and upper and side surfaces of the first insulating film are covered with a second insulating film,
and
the second electrode, the first insulating film, and the second insulating film compose a
vibrating film.

7. (Previously presented) A method for manufacturing the electret condenser of Claim 6,
wherein the first insulating film is a silicon dioxide film grown in an atmosphere at a
temperature in a range between 500 °C and 800 °C, both inclusive.

8. (Previously presented) A method for manufacturing the electret condenser of Claim 6,
wherein the second insulating film is a silicon nitride film grown in an atmosphere at a
temperature in the range between 600 °C and 800 °C, both inclusive.

9. (Cancelled)

10. (Currently Amended) The electret condenser of Claim [[9]] 6,
wherein a shape in plan of the first insulating film is smaller than a shape in plan of the
vibrating film, and
the first insulating film is arranged at a central part of the vibrating film.